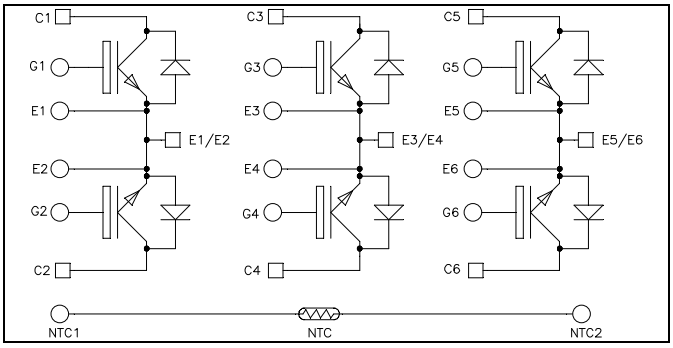
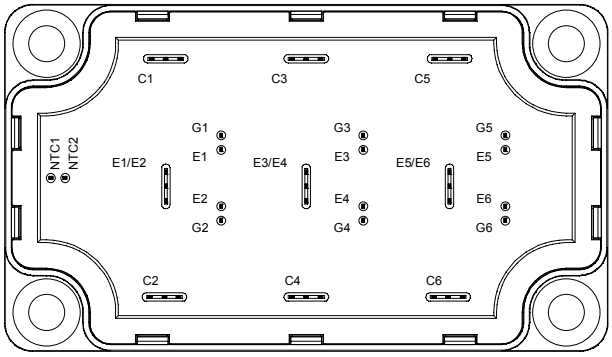
Triple Dual Common Source Trench + Field Stop IGBT4 Power module

V_{CES} = 1200V
I_C = 120A @ Tc = 80°C





Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_c = 25°C	140	A
		T_c = 80°C	120	
I_{CM}	Pulsed Collector Current	T_c = 25°C	200	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_c = 25°C	517	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 150°C	200A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				250	µA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} = 15V, I_C = 100A	T_j = 25°C		1.8	2.15	V
			T_j = 150°C		2.15		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 3.4mA		5.2	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			6.2		nF
C_{oes}	Output Capacitance				0.4		
C_{res}	Reverse Transfer Capacitance				0.35		
Q_G	Gate charge	V_{GE}= ±15V ; V_{CE}=600V I_C=100A			0.85		µC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 100A R_G = 7.5Ω			130		ns
T_r	Rise Time				20		
$T_{d(off)}$	Turn-off Delay Time				300		
T_f	Fall Time				45		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 100A R_G = 7.5Ω			150		ns
T_r	Rise Time				35		
$T_{d(off)}$	Turn-off Delay Time				350		
T_f	Fall Time				80		
E_{on}	Turn-on Switching Energy	V_{GE} = ±15V V_{Bus} = 600V I_C = 100A R_G = 7.5Ω	T_J = 25°C		5		mJ
			T_J = 150°C		10.5		
E_{off}	Turn-off Switching Energy		T_J = 25°C		5.5		mJ
			T_J = 150°C		9.5		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 900V t_p ≤10µs ; T_j = 150°C			400		A

Chopper diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C			250	µA
I_F	DC Forward Current		Tc = 80°C		120		A
V_F	Diode Forward Voltage	I_F = 100A V_{GE} = 0V	T_j = 25°C		1.9	2.4	V
			T_j = 150°C		1.85		
t_{rr}	Reverse Recovery Time	I_F = 100A V_R = 600V di/dt =2400A/µs	T_j = 25°C		155		ns
			T_j = 150°C		300		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		9.3		µC
			T_j = 150°C		20		
E_{rr}	Reverse Recovery Energy		T_j = 25°C		3.4		mJ
			T_j = 150°C		8		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.29	°C/W
			Diode			0.5	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		175	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

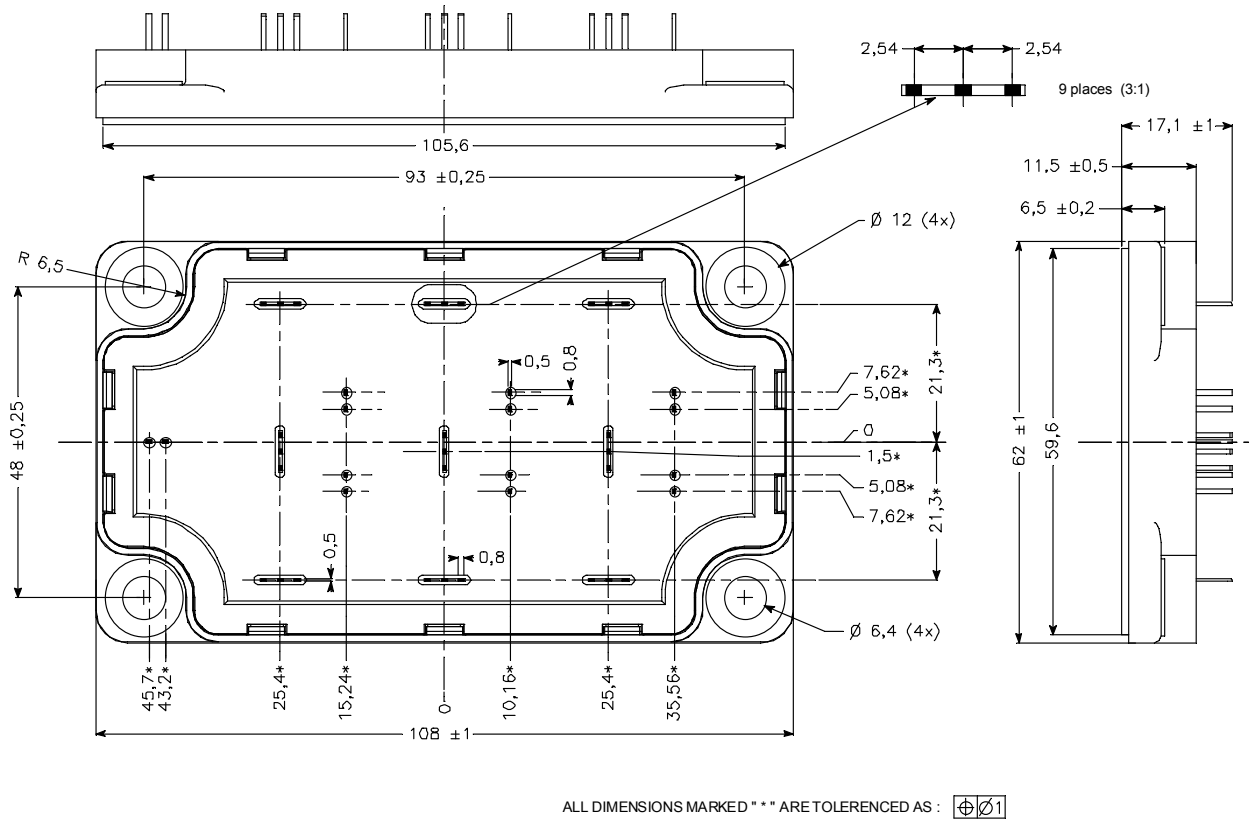
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

SP6-P Package outline (dimensions in mm)



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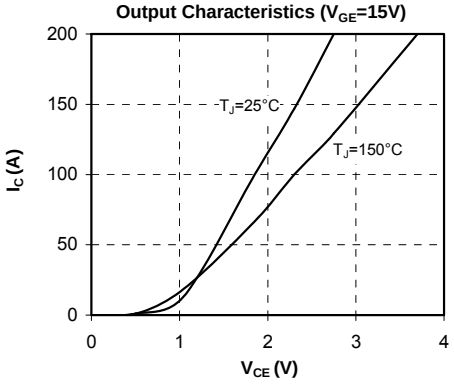
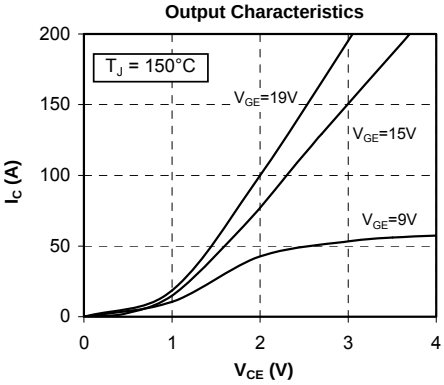
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

Typical Performance Curve

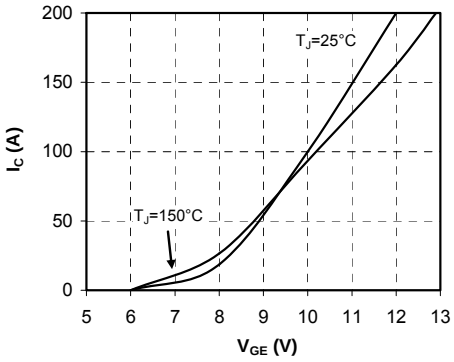
Output Characteristics (V_{GE}=15V)



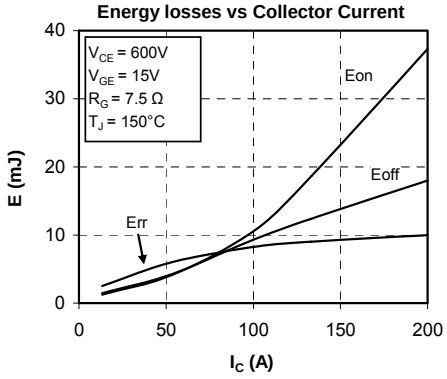
Output Characteristics



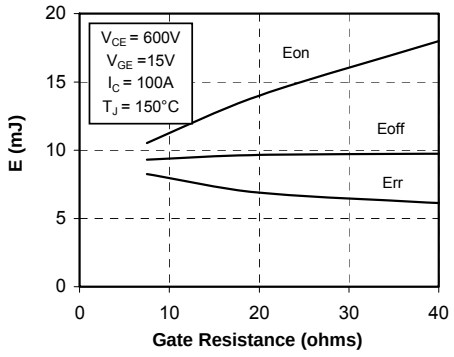
Transfert Characteristics



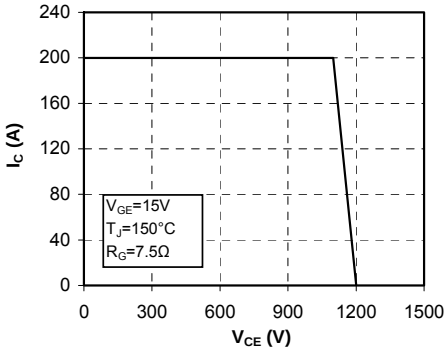
Energy losses vs Collector Current



Switching Energy Losses vs Gate Resistance



Reverse Bias Safe Operating Area



maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration